



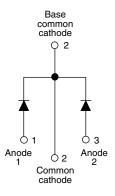
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 25 A



TO-247AC



PRODUCT SUMMARY						
Package	TO-247AC					
I _{F(AV)}	2 x 25 A					
V_{R}	600 V					
V _F at I _F	1.3 V					
t _{rr} typ.	23 ns					
T _J max.	150 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA50PA60C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A per leg continuous current, the VS-HFA50PA60C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA50PA60C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V_R		600	V			
Maximum continuous forward current per leg	1_	T _C = 100 °C	25	A			
per device	lF		50				
Single pulse forward current	I _{FSM}		225	A			
Maximum repetitive forward current	I _{FRM}		100				
Maximum power dissipation	1	T _C = 25 °C	150	W			
waximum power dissipation	P_D	T _C = 100 °C	60	VV			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			



VS-HFA50PA60CPbF, VS-HFA50PA60C-N3

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS			TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		600	-	-	
Maximum forward voltage		I _F = 25 A		-	1.3	1.7	V
	Oltage V_{FM} $I_F = 50 \text{ A}$ See fig. 1 $I_F = 25 \text{ A}, T_J = 125 \text{ °C}$	I _F = 50 A	See fig. 1	-	1.5	2.0	
			-	1.3	1.7		
Maximum reverse		V _R = V _R rated	Coo fig. 0	-	1.5	20	
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	600	2000	μΑ
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	55	100	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	12	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	I _F = 1.0 A, dI _F /dt = 200	A/μs, V _R = 30 V	-	23	-		
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	50	75	ns	
000 lig. 0, 10	t _{rr2}	T _J = 125 °C	$I_F = 25 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	105	160		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	10	A nC	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.0	15		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	112	375		
See fig. 7	Q _{rr2}	T _J = 125 °C		-	420	1200	IIC	
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	250	-	- A/µs	
	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Junction to case, single leg conducting	D		-	-	0.83			
Junction to case, both legs conducting	R _{thJC}		-	-	0.42	K/W		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount -		-	40	- r\/ vv		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-			
Weight			-	6.0	-	g		
vveignt			-	0.21	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-247AC		HFA50	PA60C			





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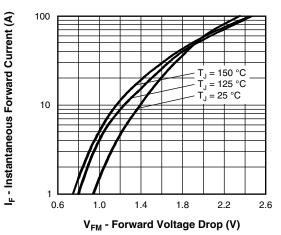


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

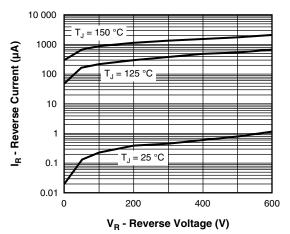


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

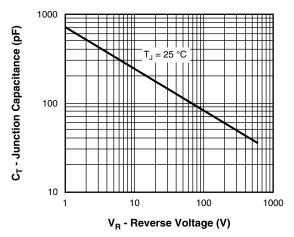


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

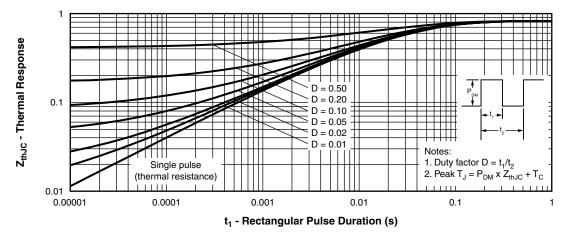


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)



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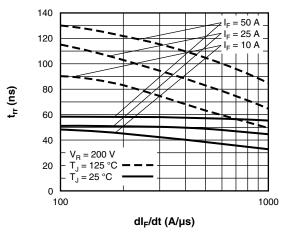


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

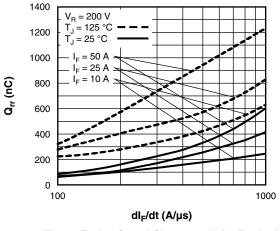


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

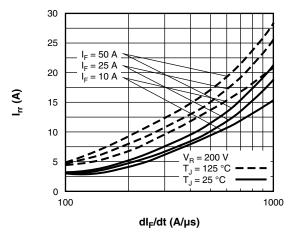


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

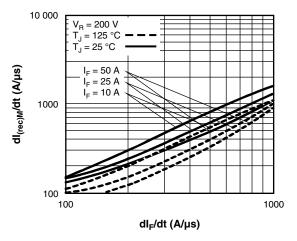


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

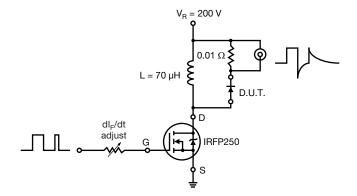
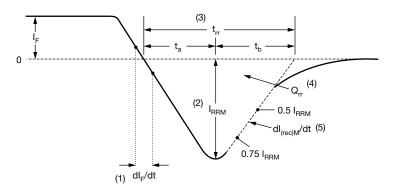


Fig. 9 - Reverse Recovery Parameter Test Circuit

VS-HFA50PA60CPbF, VS-HFA50PA60C-N3

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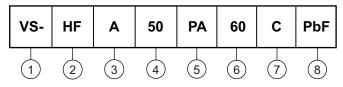


- (1) dl_F/dt rate of change of current through zero crossing
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- 3 Electron irradiated
- Current rating (50 = 50 A)
- **5** PA = TO-247AC
- 6 Voltage rating: (60 = 600 V)
- 7 Circuit configuration
 - C = common cathode
- 8 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA50PA60CPbF	25	500	Antistatic plastic tube				
VS-HFA50PA60C-N3	25	500	Antistatic plastic tube				

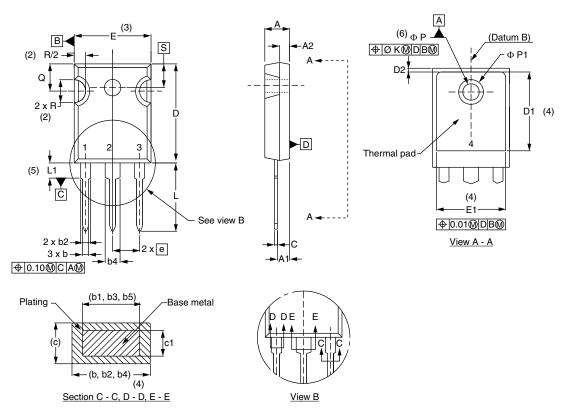
LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95542			
Dort marking information	TO-247ACPbF	www.vishay.com/doc?95226			
Part marking information	TO-247AC-N3	www.vishay.com/doc?95007			



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TO-247AC - 50 mils L/F

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
р	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIMETERS		INCHES		NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D2	0.51	1.35	0.020	0.053		
E	15.29	15.87	0.602	0.625	3	
E1	13.46	-	0.53	-		
е	5.46	BSC	0.215	BSC		
ØK	0.254		0.010			
L	14.20	16.10	0.559	0.634		
L1	3.71	4.29	0.146	0.169		
ØΡ	3.56	3.66	0.14	0.144		
Ø P1	-	7.39	-	0.291		
Q	5.31	5.69	0.209	0.224		
R	4.52	5.49	0.178	0.216		
S	5.51 BSC		0.217	BSC		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- $^{(7)}$ Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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